

In the Claims:

Please amend claims 16 and 20, please cancel claim 19, and please add claims 34-50, as indicated below.

Claims 1-15 are cancelled.

16. (Currently amended) A semiconductor device, comprising:

a low-trap-density nitrogen-containing oxide arranged upon an upper surface of a semiconductor substrate;

a high-K dielectric having a dielectric constant greater than about 5 arranged upon the nitrogen-containing oxide; and

a dielectric having a dielectric constant greater than about 20 arranged upon the high-K dielectric; and

a gate conductor arranged above the high-K dielectric.

17. (Original) The device as recited in claim 16, wherein said high-K dielectric comprises silicon nitride.

18. (Original) The device as recited in claim 16, wherein said high-K dielectric comprises a material having a dielectric constant greater than about 20.

19. (Canceled).

20. (Currently amended) The device as recited in claim 16, further comprising:

an additional gate conductor interposed between the nitrogen-containing oxide and the semiconductor substrate; and

a gate dielectric arranged interposed between the additional gate conductor and the semiconductor substrate.

21. (Original) The device as recited in claim 16, wherein said nitrogen-containing oxide has a thickness of less than about 10 angstroms.

22. (Original) The device as recited in claim 17, wherein said silicon nitride has a thickness of less than or equal to about 10 angstroms.

23. (Previously Presented) The device as recited in claim 16, wherein said high-K dielectric comprises a metal oxide having a dielectric constant greater than about 20.

24. (Previously Presented) A semiconductor device, comprising:

a low-trap-density nitrogen-containing oxide arranged upon an upper surface of a semiconductor substrate, wherein said low-trap-density nitrogen-containing oxide has a thickness of less than about 10 angstroms;

a high-K dielectric having a dielectric constant greater than about 5 arranged upon the nitrogen-containing oxide, wherein said high-K dielectric has a thickness of less than or equal to about 10 angstroms; and

a gate conductor arranged above the high K dielectric.

25. (Previously Presented) The device as recited in claim 24, wherein said high-K dielectric comprises silicon nitride.

26. (Previously Presented) The device as recited in claim 24, wherein said high-K dielectric comprises a material having a dielectric constant greater than about 20.

27. (Previously Presented) The device as recited in claim 24, wherein said high-K dielectric comprises a metal oxide having a dielectric constant greater than about 20.

28. (Previously Presented) The device as recited in claim 24, further comprising a dielectric having a dielectric constant greater than about 20 arranged upon the high-K dielectric.

29. (Previously Presented) The device as recited in claim 24, further comprising:

D' an additional gate conductor interposed between the low-trap-density nitrogen-containing oxide and the semiconductor substrate; and

a gate dielectric arranged interposed between the additional gate conductor and the semiconductor substrate.

30. (Previously Presented) The device as recited in claim 16, wherein said high-K dielectric has a low-trap-density.

31. (Previously Presented) The device as recited in claim 16, wherein said low-trap-density nitrogen-containing oxide and said high-K dielectric form a gate dielectric, wherein said gate dielectric has a low-trap-density.

32. (Previously Presented) The device as recited in claim 24, wherein said high-K dielectric has a low-trap-density.

33. (Previously Presented) The device as recited in claim 24, wherein said low-trap-density nitrogen-containing oxide and said high-K dielectric form a gate dielectric, wherein said gate dielectric has a low-trap-density.

34. (New) A semiconductor device, comprising:

a low-trap-density nitrogen-containing oxide arranged upon an upper surface of a semiconductor substrate;

a high-K dielectric having a dielectric constant greater than about 5 arranged upon the nitrogen-containing oxide, wherein said high-K dielectric has a thickness of less than or equal to about 10 angstroms; and

a conductor arranged above the high-K dielectric.

35. (New) The device as recited in claim 34, wherein said high-K dielectric comprises silicon nitride.

36. (New) The device as recited in claim 35, further comprising a dielectric having a dielectric constant greater than about 20 arranged upon the silicon nitride.

37. (New) The device as recited in claim 34, wherein said high-K dielectric comprises a material having a dielectric constant greater than about 20.

38. (New) The device as recited in claim 34, further comprising:

an additional conductor interposed between the nitrogen-containing oxide and the semiconductor substrate; and

a dielectric arranged interposed between the additional conductor and the semiconductor substrate.

39. (New) The device as recited in claim 34, wherein said high-K dielectric comprises a metal oxide having a dielectric constant greater than about 20.

40. (New) The device as recited in claim 34, wherein said high-K dielectric has a low-trap-density.

41. (New) The device as recited in claim 34, wherein said low-trap-density nitrogen-containing oxide and said high-K dielectric form a gate dielectric, wherein said gate dielectric has a low-trap-density.

42. (New) A semiconductor device, comprising:

a low-trap-density nitrogen-containing oxide arranged upon an upper surface of a semiconductor substrate;

a high-K dielectric having a dielectric constant greater than about 5 arranged upon the nitrogen-containing oxide; and

a conductor arranged directly upon the high-K dielectric.

43. (New) The device as recited in claim 42, wherein said high-K dielectric comprises silicon nitride.

44. (New) The device as recited in claim 42, wherein said high-K dielectric comprises a material having a dielectric constant greater than about 20.

45. (New) The device as recited in claim 42, further comprising:

an additional conductor interposed between the nitrogen-containing oxide and the semiconductor substrate; and

a dielectric arranged interposed between the additional conductor and the semiconductor substrate.

46. (New) The device as recited in claim 42, wherein said high-K dielectric comprises a metal oxide having a dielectric constant greater than about 20.

47. (New) The device as recited in claim 42, wherein said high-K dielectric has a low-trap-density.

DI 48. (New) The device as recited in claim 42, wherein said low-trap-density nitrogen-containing oxide and said high-K dielectric form a gate dielectric, wherein said gate dielectric has a low-trap-density.

49. (New) The device as recited in claim 42, wherein said nitrogen-containing oxide has a thickness of less than about 10 angstroms.

50. (New) The device as recited in claim 42, wherein said high-K dielectric has a thickness of less than or equal to about 10 angstroms.
